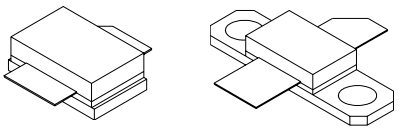
Advance Data Sheet

SL-2524

2400 MHz 25W
26.5V RF Power N-Channel Enhancement Mode LDMOS



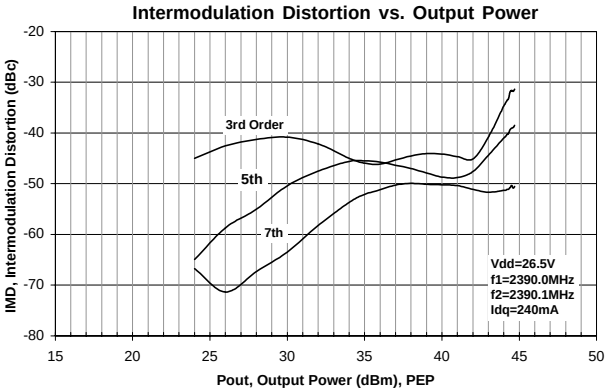
Model SL-25241 Model SL-25242

Available in pill or flange ceramic packages

Product Description

The SL-2524 is Stanford Microdevices' high-linearity 25W LDMOS transistor designed for base station applications at or near 2400 MHz. Rated for minimum output power of 25W, it is ideal for CDMA, TDMA, GSM, FM, Single or Multi-Carrier Power Amplifiers in Class A or AB operation.

Patented LDMOS Technology is used to achieve high performance and reliability at a low cost. Dual nitride passivation and gold metallization ensure excellent device performance and reliability.



Product Features

- **Patented, High Reliability LDMOS Technology**
- **Low intermodulation distortion: –30dBc at 25W (PEP).**
- **Industry Standard Packages**
- **Surface-Mountable**

Applications

- **CDMA, TDMA, GSM, FM**
- **Single/Multi-Carrier Applications in Class A or AB operation**

RF and Functional Tests
(Tc=25C unless otherwise specified, Stanford Microdevices broadband fixture)

Symbol	Rating	Unit	Min	Typ	Max
Gplin	Linear Power Gain, Single Tone (CW) (Vds=26.5V, Idq=240mA, Pout=5W, f=2400 MHz)	dB	8.5	10.0	-
Gps	Compressed Power Gain, Single Tone (CW) (Vds=26.5V, Idq=240mA, Pout=25W, f=2400 MHz)	dB	8.0	9.3	-
η	Drain Efficiency, Single Tone (CW) (Vds=26.5V, Idq=240mA, Pout=25W, f=2400 MHz)	%	35	40	-
IMD	Intermodulation Distortion, Two Tone (Vds=26.5V, Idq=225mA, Pout=25W PEP, f1=2390 MHz, f2=2390.1 MHz)	dBc	-	-32	-30
VSWR	Load Mismatch Survivability (Vds= 26.5V, Idq= 225mA, Pout=25W, f= 2400 MHz)	-	10:1	-	-

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AC Characteristics

Symbol	Rating	Unit	Min	Typ	Max
Coss	Output Capacitance (Vds=26V, Vgs=0V, f=1MHz)	pF	-	26	-
Crss	Feedback Capacitance (Vds=26V, Vgs=0V, f=1MHz)	pF	-	1.2	-

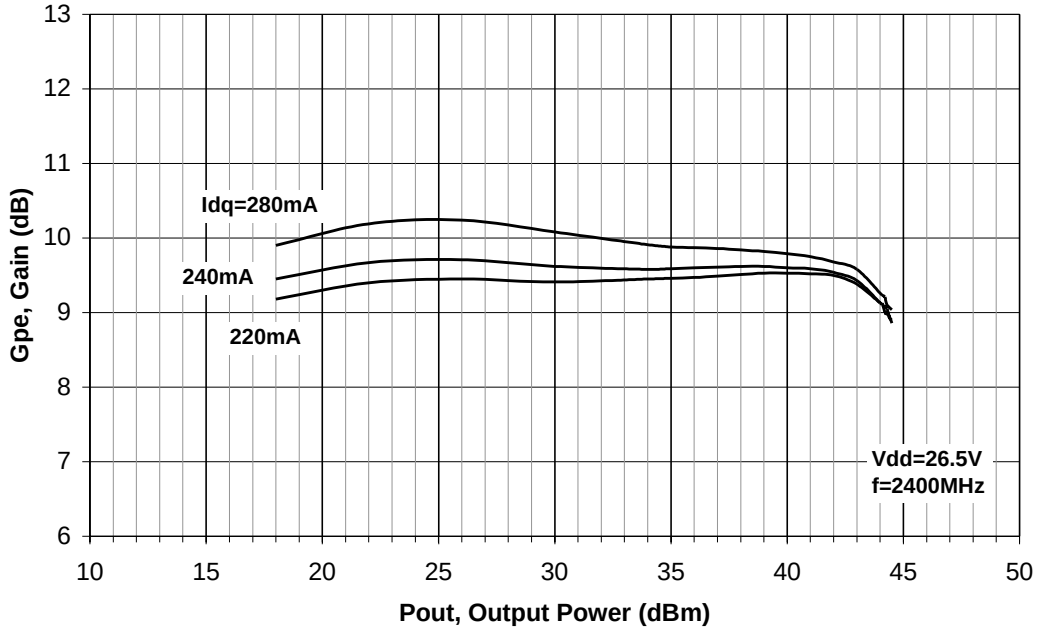
Electrical DC Characteristics(Tc=25°C unless otherwise specified)

Symbol	Characteristics	Unit	Min	Typ	Max
BVdss	Drain to Source Voltage, gate connected to source (Vgs=0V, Ids=1mA)	Volts	65	-	-
Idss	Drain to Source Leakage Current (Vds=28V, Vgs=0)	mA	-	-	1.0
Igss	Gate to Source Leakage Current (Vgs=20V, Vds=0)	uA	-	-	1.0
Vth	Threshold Voltage (Vds=10V, Ids=1mA)	Volts	2.0	3.5	5.0
Vgs (on)	Gate Quiescent Voltage (Vds=26V, Ids=200mA)	Volts	3.0	4.0	6.0
Vds (on)	Drain to Source On Voltage (Vgs=10V, Ids=1A)	Volts	-	0.28	-
Gm	Forward Transconductance (Vds=10V, Ids=5A)	S	1.4	1.8	-

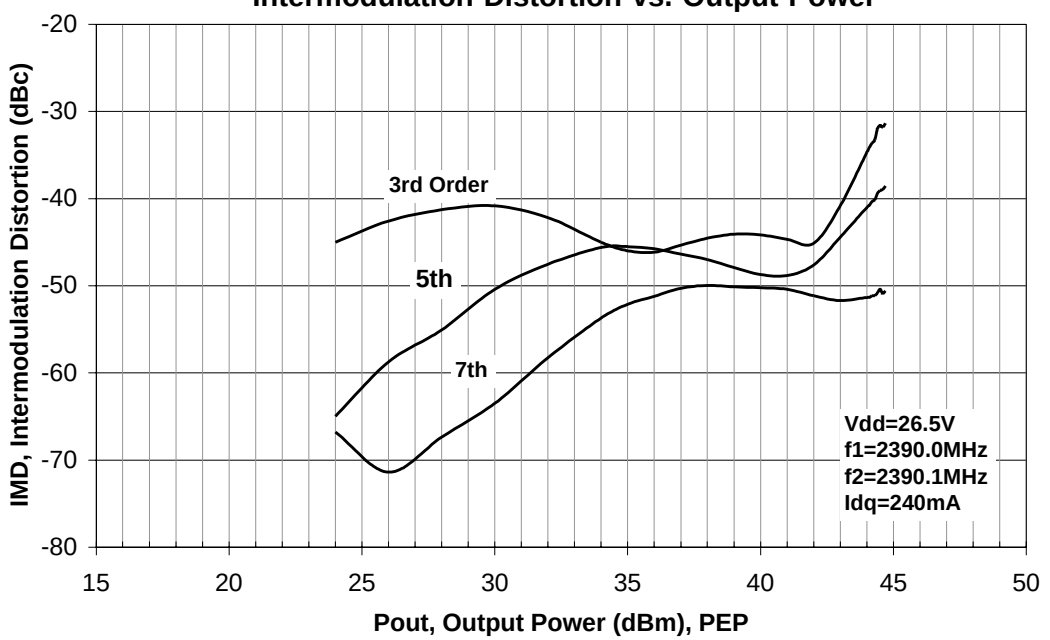
Thermal Characteristics

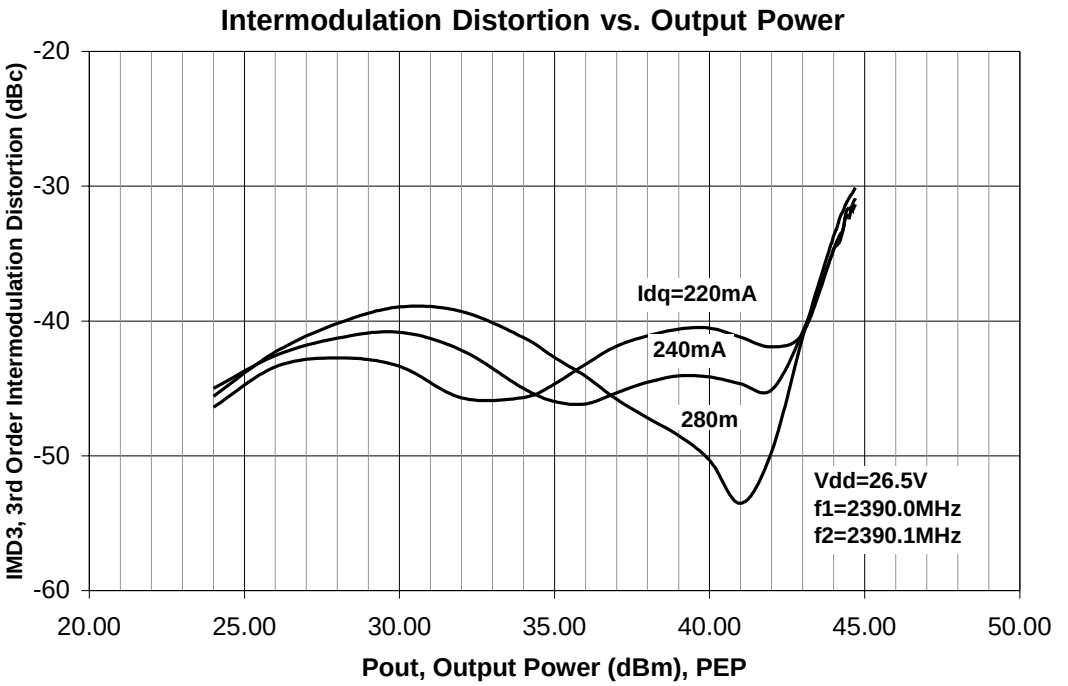
Symbol	Characteristics	Unit	Min	Typ	Max
Θjc	Thermal Resistance, Junction to Case	°C/W	-	-	2.0

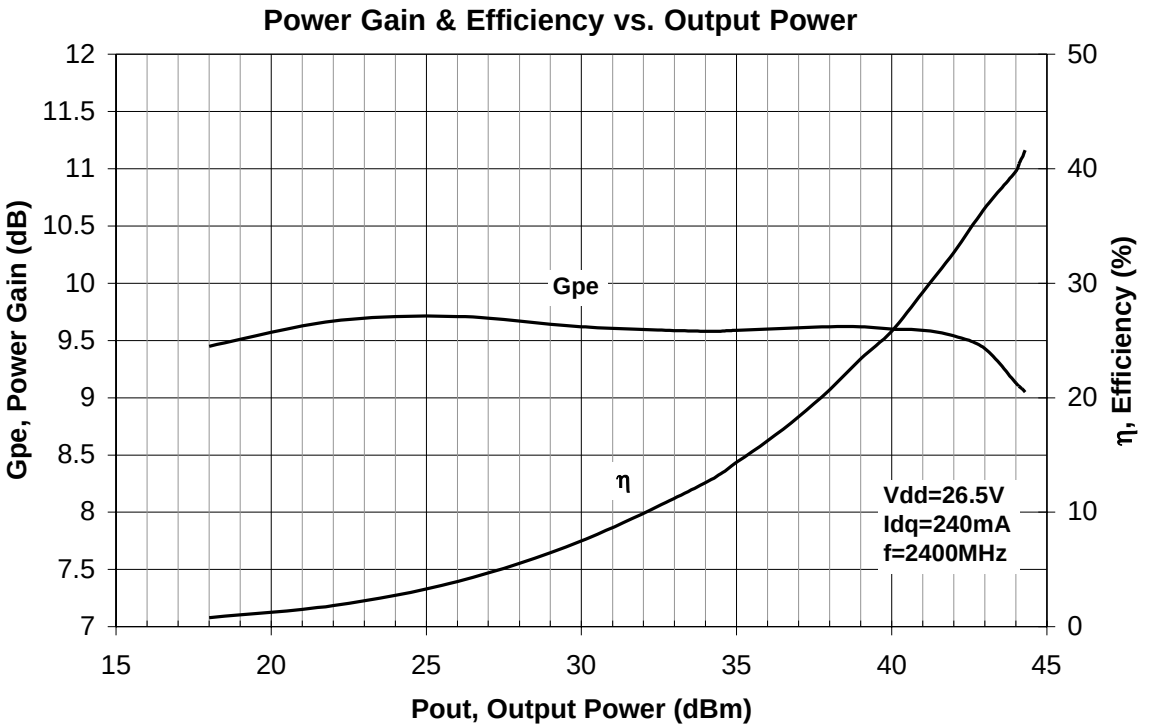
Power Gain vs. Output Power



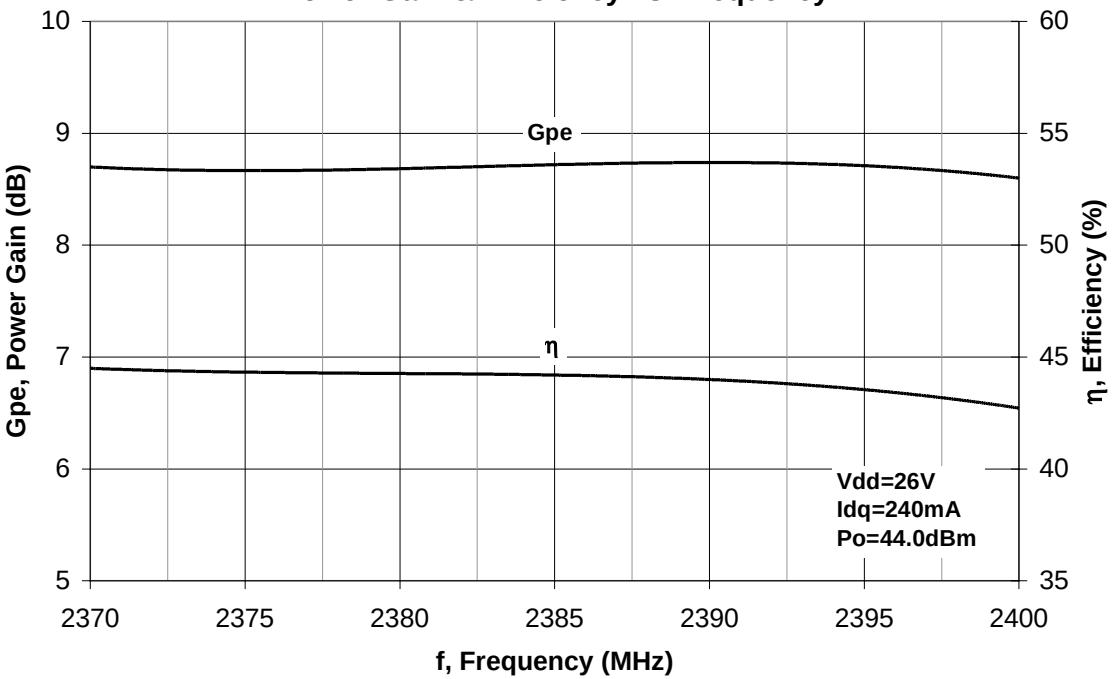
Intermodulation Distortion vs. Output Power



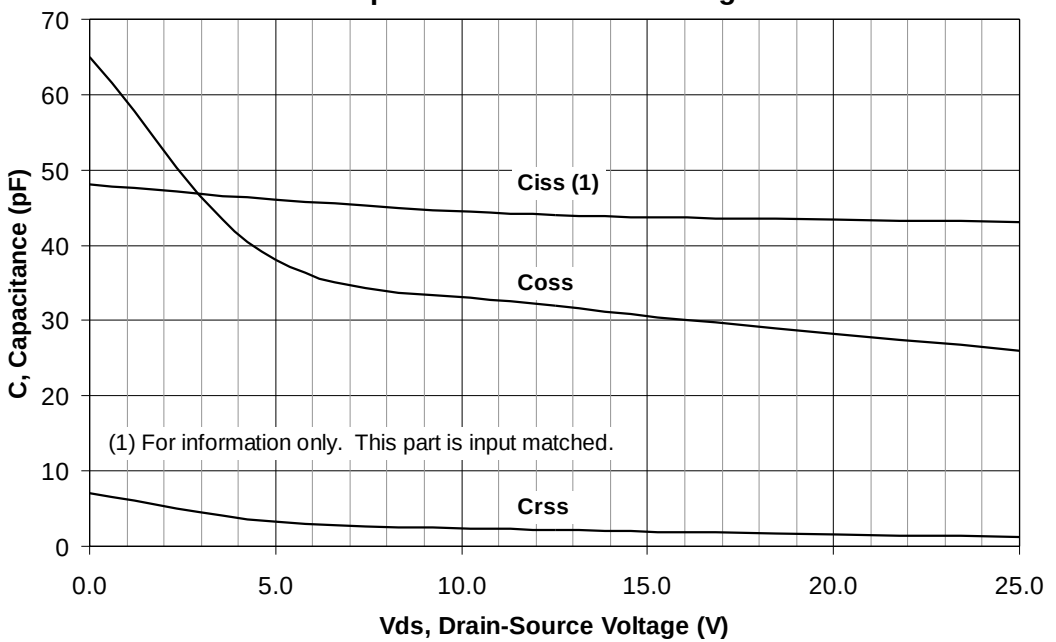

Intermodulation Distortion vs. Output Power
IMD3, 3rd Order Intermodulation Distortion (dBc)
-20
-30
-40
-50
-60
Idq=220mA
240mA
280m
Vdd=26.5V
f1=2390.0MHz
f2=2390.1MHz
20.00
25.00
30.00
35.00
40.00
45.00
50.00
Pout, Output Power (dBm), PEP


Power Gain & Efficiency vs. Output Power
Gpe, Power Gain (dB)
12
11.5
11
10.5
10
9.5
9
8.5
8
7.5
7
η, Efficiency (%)
50
40
30
20
10
0
Gpe
η
Vdd=26.5V
Idq=240mA
f=2400MHz
15
20
25
30
35
40
45
Pout, Output Power (dBm)

Power Gain & Efficiency vs. Frequency



Capacitance vs. Drain Voltage



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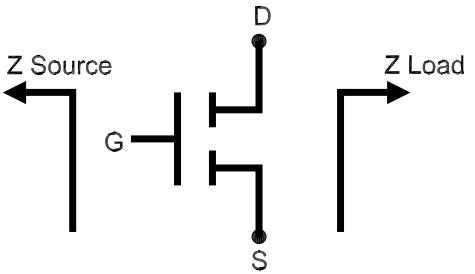
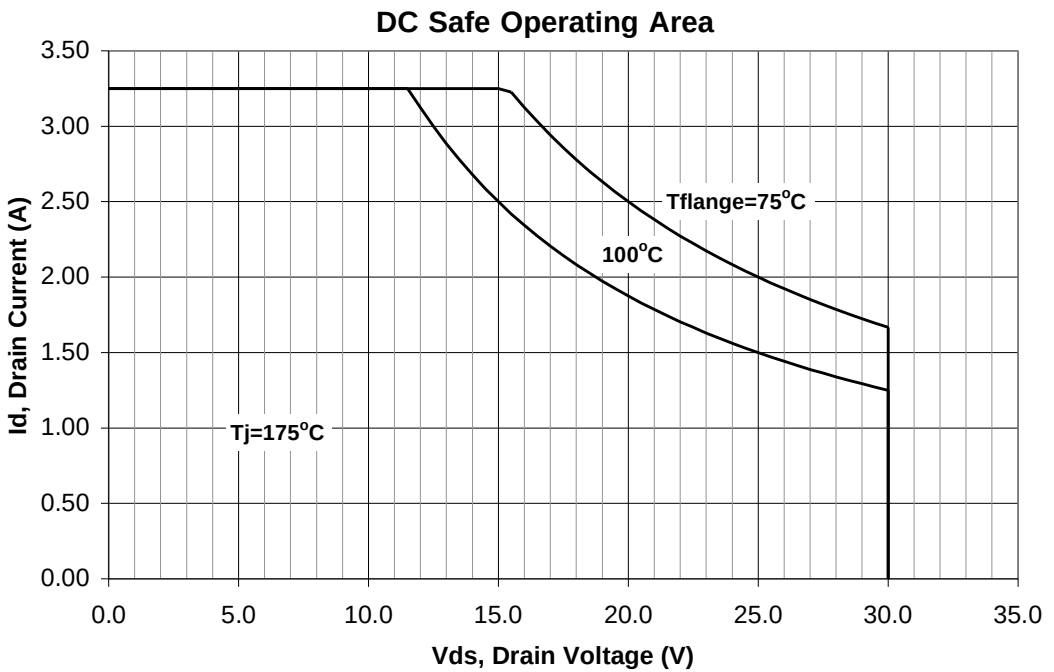
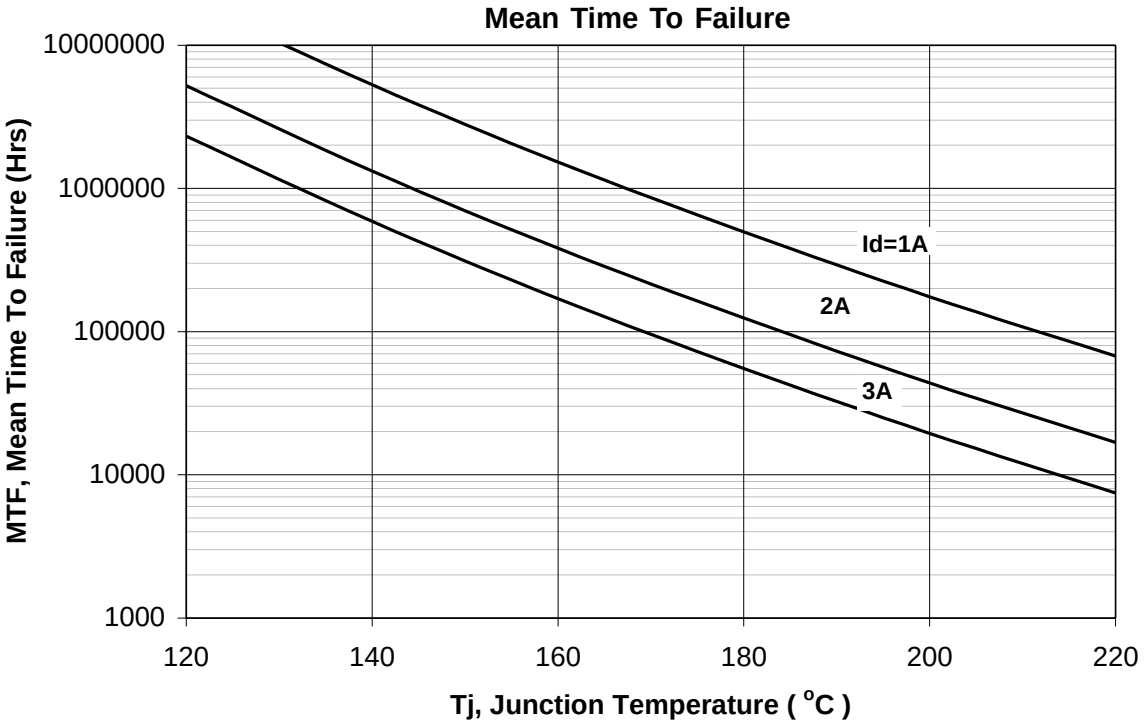


Frequency MHz	Z Source	Z Load
2340	1.54 - j3.80	0.89 - j2.23
2350	1.54 - j3.79	0.89 - j2.21
2360	1.54 - j3.77	0.89 - j2.19
2370	1.54 - j3.75	0.90 - j2.17
2380	1.53 - j3.73	0.90 - j2.15
2390	1.53 - j3.69	0.90 - j2.13
2400	1.53 - j3.69	0.90 - j2.11
2410	1.52 - j3.67	0.90 - j2.09
2420	1.52 - j3.65	0.91 - j2.07
2430	1.52 - j3.63	0.91 - j2.05
2440	1.51 - j3.62	0.91 - j2.03

Series Equivalent Input and Output Impedances, Vdd= 26V, Idq= 260mA




Mean Time To Failure
MTF, Mean Time To Failure (Hrs)
10000000
1000000
100000
10000
1000
120
140
160
180
200
220
Id=1A
2A
3A
Tj, Junction Temperature (°C)

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Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Drain to Source, gate connected to source	BVdss	65	Volts
Gate to Source Voltage	BVgs	+/- 20	Volts
Total Device Dissipation @Tcase=70°C Derate above 70°C	Pd	65 0.5	Watts W/°C
Storage Temperature Range	Tstg	-65 to +150	°C
Operating Junction Temperature	T_J	200	°C

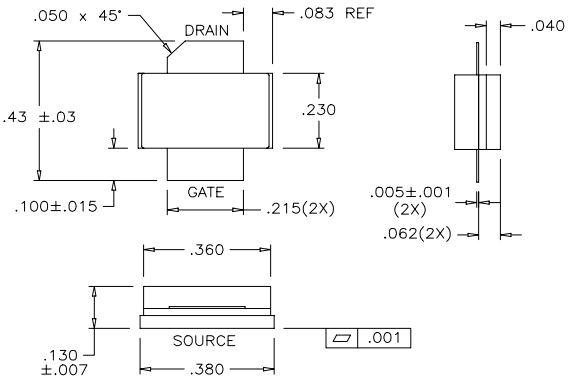
Part Number Ordering Information

Part Number	Package
SL-25241	Pill
SL-25242	Flange

Caution:

MOS Devices are susceptable to damage from ElectroStatic Discharge (ESD). Appropriate precautions in handling, packaging and testing MOS devices must be observed.

Pill Package



Note:
1) Cut lead identifies drain.
2) Dimensions are in inches.
3) Tolerances:
   .XX +/- .01
   .XXX +/- .005

Flange Package